

Christopher M Smyth

List of Publications by Year in descending order

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papers

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#	ARTICLE	IF	CITATIONS
1	Controlling the Pd Metal Contact Polarity to Trigonal Tellurium by Atomic Hydrogen Removal of the Native Tellurium Oxide. <i>Advanced Materials Interfaces</i> , 2021, 8, 2002050.	3.7	10
2	Modification of the Electronic Transport in Atomically Thin WSe_2 by Oxidation. <i>Advanced Materials Interfaces</i> , 2020, 7, 2000422.	3.7	11
3	Origins of Fermi Level Pinning between Tungsten Dichalcogenides (WS_2 , WTe_2) and Bulk Metal Contacts: Interface Chemistry and Band Alignment. <i>Journal of Physical Chemistry C</i> , 2020, 124, 14550-14563.	3.1	19
4	<i>In situ</i> exfoliated 2D molybdenum disulfide analyzed by XPS. <i>Surface Science Spectra</i> , 2020, 27, .	1.3	21
5	Impact of Etch Processes on the Chemistry and Surface States of the Topological Insulator Bi_2Se_3 . <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 32144-32150.	8.0	9
6	Origins of Fermi-Level Pinning between Molybdenum Dichalcogenides ($MoSe_2$), Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 547 <i>Physical Chemistry C</i> , 2019, 123, 23919-23930.	3.1	20
7	Contact Engineering High-Performance n-Type $MoTe_2$ Transistors. <i>Nano Letters</i> , 2019, 19, 6352-6362.	9.1	87
8	2D bismuth telluride analyzed by XPS. <i>Surface Science Spectra</i> , 2019, 26, .	1.3	6
9	2D topological insulator bismuth selenide analyzed by in situ XPS. <i>Surface Science Spectra</i> , 2019, 26, 024014.	1.3	3
10	Contact Engineering for Dual-Gate MoS_2 Transistors Using O_2 Plasma Exposure. <i>ACS Applied Electronic Materials</i> , 2019, 1, 210-219.	4.3	40
11	Engineering the Palladium- WSe_2 Interface Chemistry for Field Effect Transistors with High-Performance Hole Contacts. <i>ACS Applied Nano Materials</i> , 2019, 2, 75-88.	5.0	24
12	One dimensional metallic edges in atomically thin WSe_2 induced by air exposure. <i>2D Materials</i> , 2018, 5, 025017.	4.4	47
13	Covalent nitrogen doping in molecular beam epitaxy-grown and bulk WSe_2 . <i>APL Materials</i> , 2018, 6, .	5.1	21
14	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. <i>ACS Nano</i> , 2018, 12, 965-975.	14.6	172
15	High-Mobility Helical Tellurium Field-Effect Transistors Enabled by Transfer-Free, Low-Temperature Direct Growth. <i>Advanced Materials</i> , 2018, 30, e1803109.	21.0	71
16	WSe_2 -contact metal interface chemistry and band alignment under high vacuum and ultra high vacuum deposition conditions. <i>2D Materials</i> , 2017, 4, 025084.	4.4	77
17	Intrinsic air stability mechanisms of two-dimensional transition metal dichalcogenide surfaces: basal versus edge oxidation. <i>2D Materials</i> , 2017, 4, 025050.	4.4	87
18	Interface Chemistry of Contact Metals and Ferromagnets on the Topological Insulator Bi_2Se_3 . <i>Journal of Physical Chemistry C</i> , 2017, 121, 23551-23563.	3.1	71

#	ARTICLE	IF	CITATIONS
19	Test structures for understanding the impact of ultra-high vacuum metal deposition on top-gate MoS ₂ field-effect-transistors. , 2017, , .		1
20	Contact Metal-MoS ₂ Interfacial Reactions and Potential Implications on MoS ₂ -Based Device Performance. Journal of Physical Chemistry C, 2016, 120, 14719-14729.	3.1	114